## |查询"MMBT2222AK"供应商

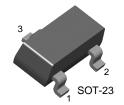


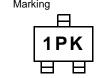
February 2005

# MMBT2222AK

# **NPN Epitaxial Silicon Transistor**

## **General Purpose Transistor**





1. Base 2. Emitter 3. Collector

## **Absolute Maximum Ratings** $T_a = 25$ °C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	75	V
$V_{CEO}$	Collector-Emitter Voltage	40	V
$V_{EBO}$	Emitter-Base Voltage	6	V
I <sub>C</sub>	Collector Current	600	mA
$P_{C}$	Collector Power Dissipation	350	mW
T <sub>STG</sub>	Storage Temperature	150	°C

# **Electrical Characteristics** $T_a$ =25°C unless otherwise noted

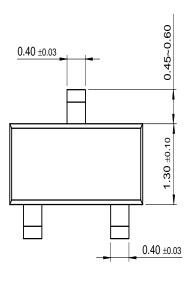
Symbol	Parameter	Test Condition	Min.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 10\mu A, I_E = 0$	75		V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0	40		V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 10\mu A, I_C = 0$	6		V
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> = 60V, I <sub>E</sub> = 0		0.01	μΑ
h <sub>FE</sub>	DC Current Gain *	$V_{CE} = 10V, I_C = 0.1 mA$ $V_{CE} = 10V, I_C = 1 mA$ $V_{CE} = 10V, I_C = 10 mA$ $V_{CE} = 10V, I_C = 150 mA$ $V_{CE} = 10V, I_C = 500 mA$	35 50 75 100 40	300	
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage *	I <sub>C</sub> = 150mA, I <sub>B</sub> = 15mA I <sub>C</sub> = 500mA, I <sub>B</sub> = 50mA		0.3 1.0	V V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage *	I <sub>C</sub> = 150mA, I <sub>B</sub> = 15mA 0.6 I <sub>C</sub> = 500mA, I <sub>B</sub> = 50mA		1.2 2.0	V V
f <sub>T</sub>	Current Gain Bandwidth Product	I <sub>C</sub> = 20mA, V <sub>CE</sub> = 20V, f = 100MHz 300		MHz	
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> = 10V, I <sub>E</sub> = 0, f = 1MHz 8		pF	
NF	Noise Figure	$\begin{split} I_C &= 100 \mu A, \ V_{CE} = 10 V \\ R_S &= 1 K \Omega, \ f = 1 M H z \end{split} \tag{4}$		4	dB
t <sub>ON</sub>	Turn On Time	$V_{CC} = 30V, I_C = 150mA$ $V_{BE} = 0.5V, I_{B1} = 15mA$ 35		ns	
t <sub>OFF</sub>	Turn Off Time	$V_{CC} = 30V, I_C = 150mA,$ 285 $I_{B1} = I_{B2} = 15mA$		ns	

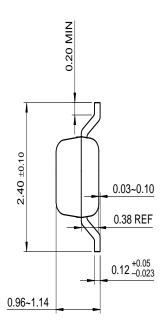
<sup>\*</sup> Pulse Test: Pulse Width $\leq$ 300 $\mu$ s, Duty Cycle $\leq$ 2%

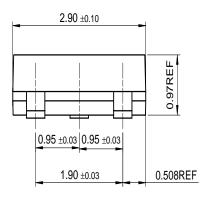
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## **Mechanical Dimensions**

# SOT-23







Dimensions in Millimeters

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